4-A/7-A, Opto-Compatible 1-CH Isolated Gate Driver

Features

- Single-Channel Isolated Gate Driver with Optocoupler-Compatible Input
- 4-A Source/7-A Sink Peak Output Current with Rail-to-Rail Output
- 35-V Output Driver Supply Voltage
- 4-V, 6-V, 8-V and 12-V V_{CC} UVLO Options
- 5.7-V Reverse Polarity Voltage Handling Capability on Input Stage
- Ultra-Fast Output Driving
  - 105-ns Propagation Delay
  - 25-ns Delay Matching
  - 35-ns Pulse Width Distortion
- 5-kV_{RMS} Reinforced Isolation Rating
- ±150-kV/μs Common-Mode Transient Immunity (CMTI)
- Industrial Standard Wide-Body WSOP6 Package
- Operating Ambient Temperature T_A −40°C to +125°C
- Safety-Related Certifications: (In progress)
  - DIN EN IEC 60747-17(VDE 0884-17): 2021-10 (In progress)
  - 5-kV_{RMS} Isolation Rating per UL 1577 (In progress)
  - CSA Component Acceptance Service Notice 5A (In progress)
  - CQC Certification per GB 4943.1-2022 (In progress)

Applications

- Industrial Motor-Control Drives
- Industrial Power Supplies, UPS
- Solar Inverters
- Induction Heating

Description

The TPM23525 driver is a single-channel isolated gate driver for IGBTs, MOSFETs, and SiC MOSFETs. Its input is optocoupler-compatible and uses the industry-standard wide-body WSOP6 package. Its driving capability can support a 5-A source and 5-A sink current. The output stage can withstand high voltages up to 35 V and supports the latest generation of IGBT and SiC-based applications.

The TPM23525 device provides high electromagnetic immunity and low emissions at low power consumption. Its isolation channel is separated by a double-capacitive silicon dioxide (SiO2) insulation barrier. 3PEAK proprietary galvanic isolation technology supports 150 kV/μs common-mode transient immunity (CMTI), which is critical especially for SiC applications. The TPM23525 input stage emulates an opto-diode with enhanced noise immunity. Its enhanced reliability can support high-power industrial applications.

Typical Application Circuit

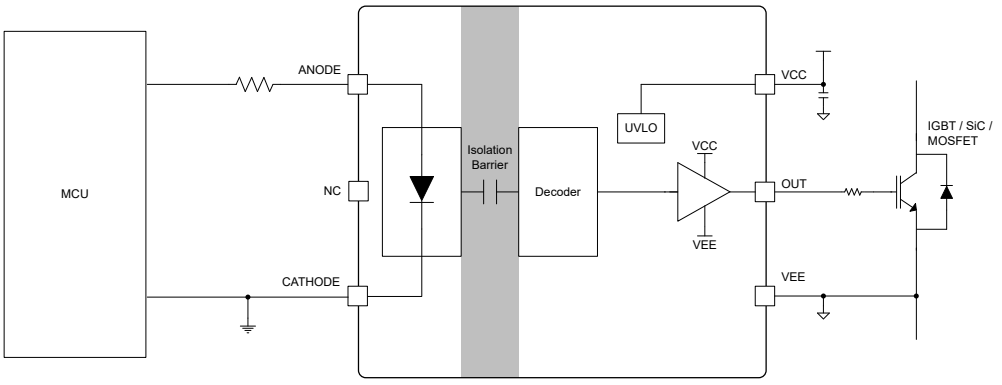


Table of Contents

Product Family Table

Order Number	UVLO Threshold (V)	Package
TPM23525A-SOER	6.3	WSOP6
TPM23525B-SOER	8.9	WSOP6
TPM23525C-SOER	13.3	WSOP6
TPM23525D-SOER	4.5	WSOP6

Revision History

Date	Revision	Notes
2026-04-18	Rev.A.0	Initial release

Pin Configuration and Functions

TPM23525
WSOP6
Top View

Table 1. Pin Functions: TPM23525

Pin		I/O	Description
No.	Name		
1	ANODE	I	Emulated diode anode input
2	NC	–	No Connection
3	CATHODE	O	Emulated diode cathode input
4	VEE	P	Output power ground
5	VOUT	O	Gate driver output
6	VCC	P	Output power supply

Specifications

Absolute Maximum Ratings (1)

Parameter		Min	Max	Unit
Input Voltage	Reverse Input Voltage, CATHODE – ANODE		8.25	V
	Average Transient Input Current, $I_{F(AVG)}$		25	mA
	Peak Transient Input Current, $I_{F(TRAN)}$		1	A
Output Voltage	Output Supply Voltage, V_{CC} − V_{EE}	−0.3	35	V
	V_{OUT}	V_{EE} − 0.3	V_{CC} + 0.3	V
T_J	Maximum Junction Temperature	−40	150	°C
T_A	Operating Ambient Temperature Range	−40	125	°C
T_{STG}	Storage Temperature Range	−65	150	°C
T_L	Lead Temperature (Soldering, 10 sec)		260	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.
(2) This data was taken with the JEDEC low effective thermal conductivity test board.
(3) This data was taken with the JEDEC standard multilayer test boards.

ESD, Electrostatic Discharge Protection

Parameter		Condition	Minimum Level	Unit
HBM	Human Body Model ESD	ANSI/ESDA/JEDEC JS-001 (1)	±3	kV
CDM	Charged Device Model ESD	ANSI/ESDA/JEDEC JS-002 (2)	±1.5	kV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Recommended Operating Conditions

Parameter		Min	Max	Unit
V_{CC} – V_{EE}	Output Supply Voltage (TPM23525C 12V UVLO)	13.5	33	V
V_{CC} – V_{EE}	Output Supply Voltage (TPM23525B 8V UVLO)	9	33	V
V_{OUT}	Output Voltage	V_{EE}	V_{CC}	V
$I_{F(ON)}$	Input Diode Forward Current, on-state	5	20	mA
$V_{F(OFF)}$	Input Diode Forward Voltage, off-state	−6	0.9	V
T_J	Junction Temperature	−40	150	°C
T_A	Operating Ambient Temperature	−40	125	°C

Thermal Information

Package	θ_{JA}	θ_{JB}	$\theta_{JC\text{-}top}$	Unit
WSOP6	117.19	61.67	53.95	°C/W

Safety Limiting Values

Parameter		Test Conditions	Min	Typ	Max	Unit
I_S	Safety input, output, or supply current	R_{QJA} = 120 °C/W, V_I = 15 V, T_J = 150 °C, T_A = 25 °C			50	mA
		R_{QJA} = 120 °C/W, V_I = 30 V, T_J = 150 °C, T_A = 25 °C			25	
P_S	Safety input, output, or total power	R_{QJA} = 120 °C/W, T_J = 150 °C, T_A = 25 °C			750	mW
T_S	Maximum safety temperature				150	°C

Insulation Specifications

Parameter		Conditions	Value	Unit
CLR	External Clearance	Shortest terminal-to-terminal distance through air	> 8.5	mm
CPG	External Creepage	Shortest terminal-to-terminal distance across the package surface	> 8.5	mm
DTI	Distance through the Insulation	Minimum internal gap (internal clearance)	> 22	μm
CTI	Comparative Tracking Index		> 600	V
	Material Group		I	
	Installation Classification	For Rated Mains Voltage ≤ 300 V_{RMS}	I-III	
	Pollution Degree		2	
	Climate Category		40/125/21	
C_{IO}	Isolation Capacitance	V_{IO} = 0.4 × sin (2πft), f = 1 MHz	0.5	pF
R_{IO}	Isolation Resistance	V_{IO} = 500 V, T_A = 25 °C	> 10^9	Ω
		V_{IO} = 500 V, 100°C ≤ T_A ≤ 125 °C	> 10^{10}	
		V_{IO} = 500 V, T_A = 150 °C	> 10^{11}	
V_{IORM}	Maximum Repetitive Isolation Voltage	AC voltage (bipolar)	1500	V_{PK}
V_{IOWM}	Maximum Working Isolation Voltage	AC voltage; TDDB Test	1060	V_{RMS}
		DC voltage	1500	V_{DC}
V_{IOTM}	Maximum Transient Isolation Voltage	V_{TEST} = V_{IOTM}, t = 60 s (qualification);	8000	V_{PK}
		V_{TEST} = 1.2 x V_{IOTM}, t = 1 s (100% production)	7070	V_{PK}
V_{IOSM}	Maximum Surge Isolation Voltage	Test method per IEC 62368-1, 1.2/50 μs waveform, V_{TEST} = 1.3 × V_{IOSM} (qualification) = 10000	7690	V_{PK}
V_{ISO}	UL 1577 Withstand Isolation Voltage	V_{TEST} = V_{ISO} = 5000 V_{RMS}, t = 60 s (in qualification), V_{TEST} = 1.2 × V_{ISO}- 6000 V_{RMS}, t = 1 s (100% in production)	5000	V_{RMS}
q_{pd}	Apparent Charge	Method a, After the Input/Output safety test subgroup 2/3, V_{ini} = V_{IOTM}, t_{ini} = 60 s; $V_{pd(m)}$ = 1.2 × V_{IORM}, t_m = 10 s	≤ 5	pC
		Method a, After environmental tests subgroup 1, V_{ini} = V_{IOTM}, t_{ini} = 60 s; $V_{pd(m)}$ = 1.6 × V_{IORM}, t_m = 10 s	≤ 5	
		Method b1; At routine test (100% production) and preconditioning (type test), V_{ini} = 1.2 x V_{IOTM}, t_{ini} = 1 s; $V_{pd(m)}$ = 1.875 × V_{IORM}, t_m = 1 s	≤ 5	

(1) All pins on each side of the barrier tied together create a two-terminal device.

Electrical Characteristics

All test conditions: V_{CC} − V_{EE} = 14 to 33 V, V_{EE} referred as GND, T_A = −40°C to 125°C, unless otherwise noted.

Parameter		Conditions	Min	Typ	Max	Unit
Input						
I_{FTH_R}	Input Forward Threshold Current, Rising Edge	V_{OUT} > 5 V	0.8	1.7	3	mA
V_F	Input Forward Voltage	I_F = 10 mA	1.7	2.05	2.4	V
		I_F = 5 mA		1.95		V
V_{FTH_F}	Input Threshold Voltage, falling edge	V_{OUT} < 5 V	0.9	1.4	1.7	V
$\Delta V_F/\Delta T$	Input Forward Voltage, Temperature Coefficient	I_F = 10 mA		0.9		mV/°C
V_R	Input Reverse Breakdown Voltage	I_R = 10 μA	8.25			V
C_{IN}	Input Parasitic Capacitance	F = 0.5 MHz		15		pF
Output						
I_{OH}	Output Source Peak Current (1)	I_F = 10 mA, V_{CC} = 15 V, C_{LOAD} = 0.22 μF, V_{CC} = 10 μF, f = 1 kHz		4		A
I_{OL}	Output Sink Peak Current (1)	I_F = 10 mA, V_{CC} = 15 V, C_{LOAD} = 0.22 μF, V_{CC} = 10 μF, f = 1 kHz		7		A
V_{OH}	Output Voltage, V_{CC} − V_{OUT}	OUT = H, I_{OUT} = −20 mA	40	80	150	mV
V_{OL}	Output Voltage, V_{OUT} − V_{EE}	OUT = L, I_{OUT} = 20 mA		8	25	mV
I_{CC_H}	Output Quiescent Current, OUT = H	OUT = H, I_{OUT} = 0 mA	0.55	0.92	1.7	mA
I_{CC_L}	Output Quiescent Current, OUT = L	OUT = L, I_{OUT} = 0 mA	0.5	0.82	1.5	mA
V_{OUTPD}	Output Active Pull Down on Output	I_{OUT} = 200mA, VCC floating and unpowered.		1.85	2.2	V
Under Voltage Lockout, TPM23525C (12-V UVLO Version)						
V_{UVLO_R}	Under Voltage Lock-out Threshold, Rising Edge	OUT = H	11.7	12.5	13.3	V
V_{UVLO_F}	Under Voltage Lock-out Threshold, Falling Edge		10.7	11.5	12.3	V
V_{UVLO_HYS}	UVLO Hysteresis			1		V
Under Voltage Lockout, TPM23525B (8-V UVLO Version)						
V_{UVLO_R}	Under Voltage Lock-out Threshold, Rising Edge	OUT = H	7.7	8.5	9.8	V
V_{UVLO_F}	Under Voltage Lock-out Threshold, Falling Edge		7.2	7.9	8.4	V

Parameter		Conditions	Min	Typ	Max	Unit
V_{UVLO_HYS}	UVLO Hysteresis			0.6		V

(1) Guaranteed by design

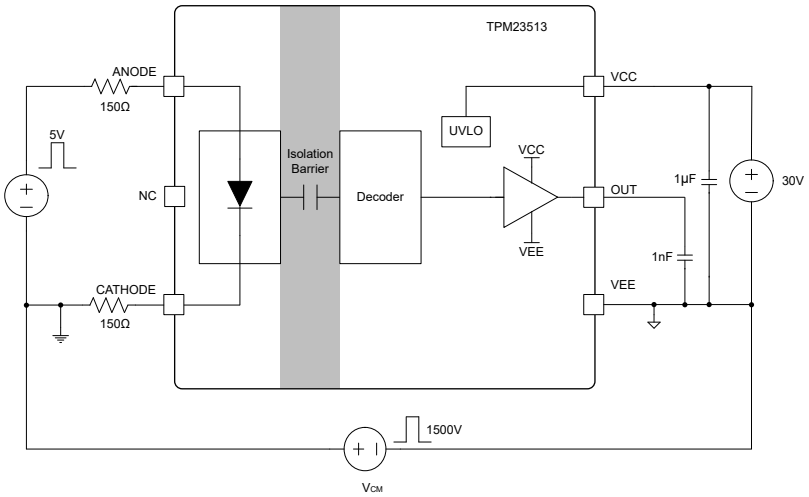
Timing Characteristics

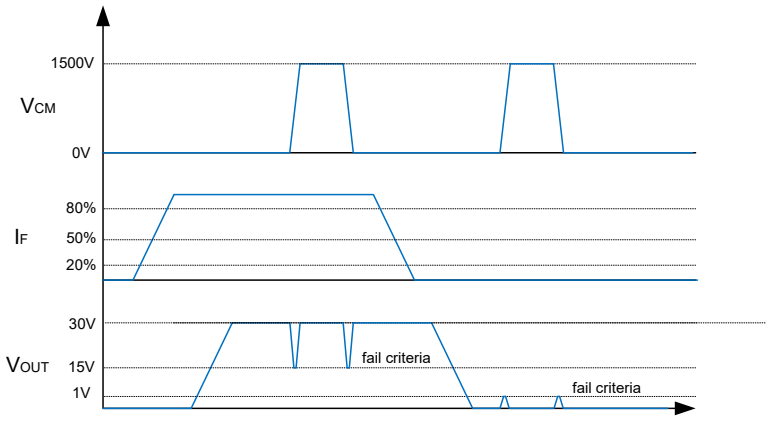
Parameter		Test Conditions	Min	Typ	Max	Unit
t_r	Output Rise Time (1)	F_{SW} = 20 kHz, (50% Duty Cycle) V_{CC} = 15 V		8.2	28	ns
t_f	Output Fall Time (1)			6.5	25	ns
t_{PLH}	Propagation Delay, Low to High			75	105	ns
t_{PHL}	Propagation Delay, High to Low			77	105	ns
t_{PWD}	Pulse Width Distortion $\|t_{PHL} - t_{PLH}\|$			2	35	ns
$t_{sk(pp)}$	Part-to-Part Skew in Propagation Delay between any Two Parts (1)	F_{SW} = 20 kHz, (50% Duty Cycle) V_{CC} = 15 V, I_F = 10 mA			25	ns
t_{UVLO_rec}	UVLO Recovery Delay	V_{CC} Rising from 0 V to 15 V		8.5	15	µs
$CMTI_H$	Common-mode Transient Immunity (Output High) (1)	I_F= 10 mA, V_{CM} = 1500 V, VCC = 30 V, T_A = 25 °C	150			kV/µs
$CMTI_L$	Common-mode Transient Immunity (Output Low) (1)	V_F= 0 V, V_{CM} = 1500 V, VCC = 30 V, T_A = 25 °C	150			kV/µs

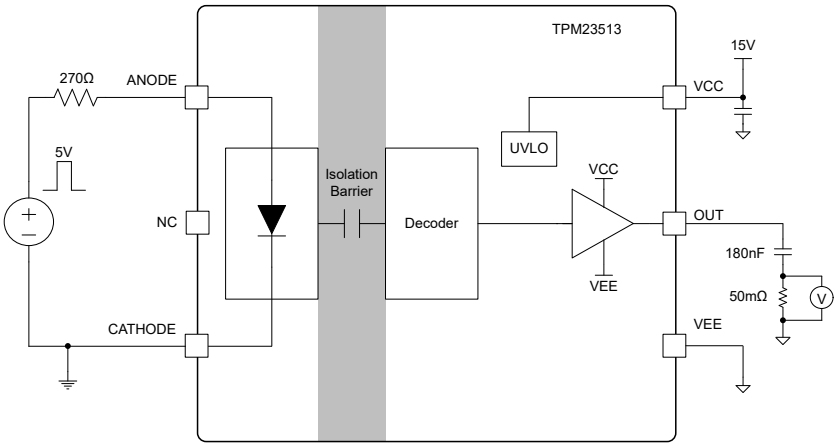
(1) Guaranteed by design

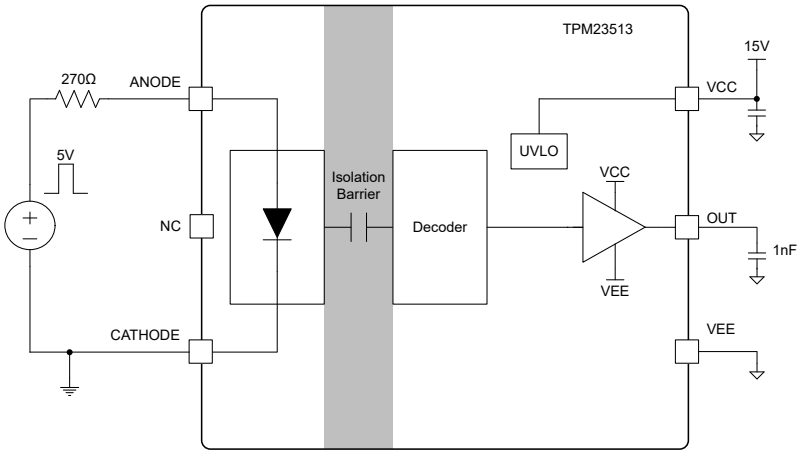
Parameter Measurement

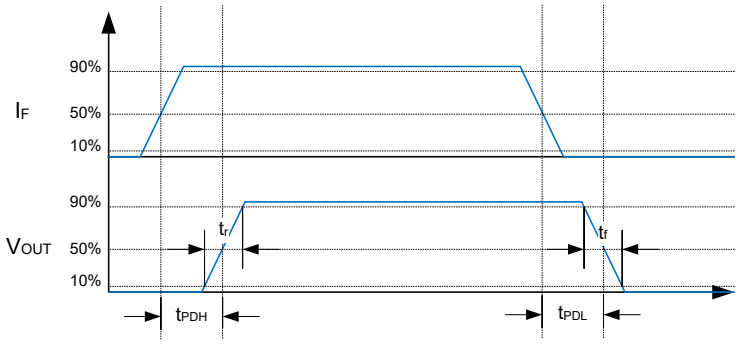
Driver Parameter




1500V
VCM
0V
80%
IF
50%
20%
30V
VOUT
15V
1V
fail criteria
fail criteria


TPM23513
15V
270Ω
ANODE
VCC
5V
UVLO
VCC
Isolation Barrier
NC
Decoder
OUT
180nF
VEE
50mΩ
V
CATHODE
VEE


TPM23513
15V
270Ω
ANODE
VCC
5V
UVLO
VCC
Isolation Barrier
NC
Decoder
OUT
1nF
VEE
CATHODE
VEE


IF
90%
50%
10%
VOUT
90%
50%
10%
tr
tf
tPDH
tPDL

Typical Performance Characteristics

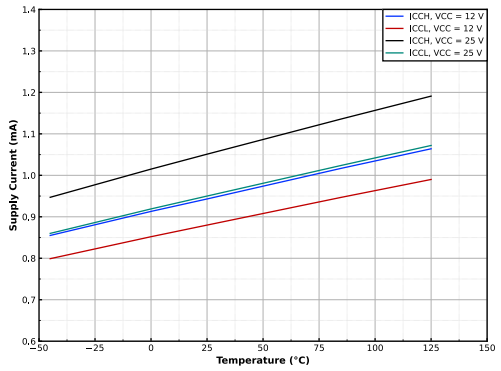


Figure 1. Start-up Current vs. Temperature

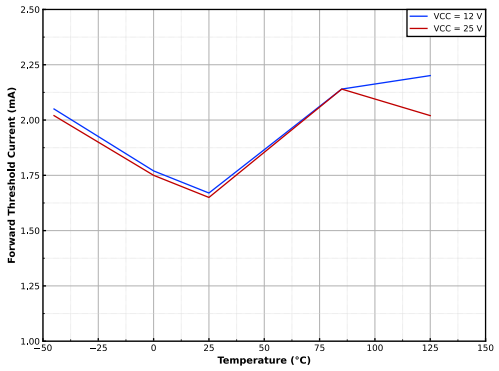


Figure 2. Forward Threshold Current vs. Temperature

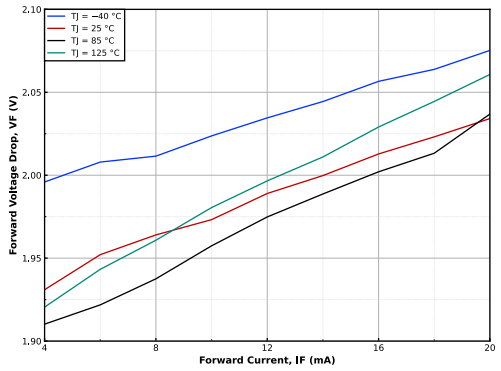


Figure 3. Forward Voltage Drop vs. Forward Current

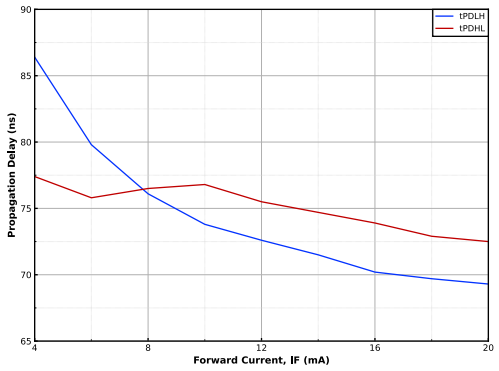
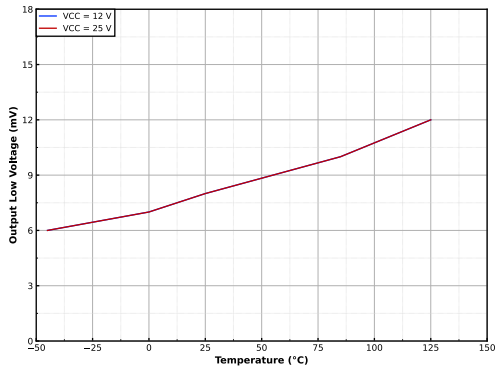
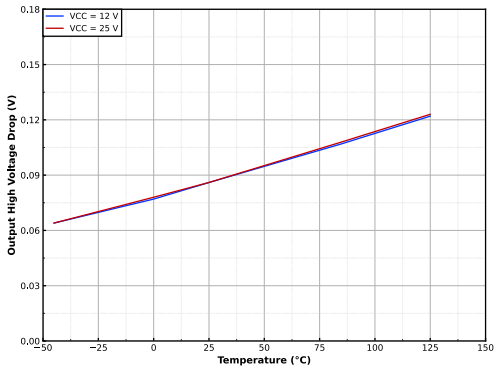


Figure 4. Propagation Delay vs. Forward Current



I_{OUT} = −20 mA

Figure 5. V_{OL} Voltage Drop vs. Temperature



I_{OUT} = 20 mA

Figure 6. V_{OH} Voltage Drop vs. Temperature

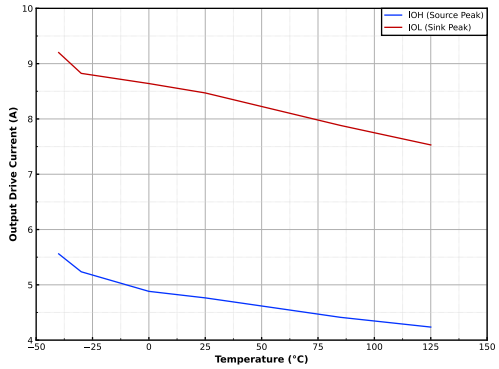


Figure 7. Output Drive Current vs. Temperature

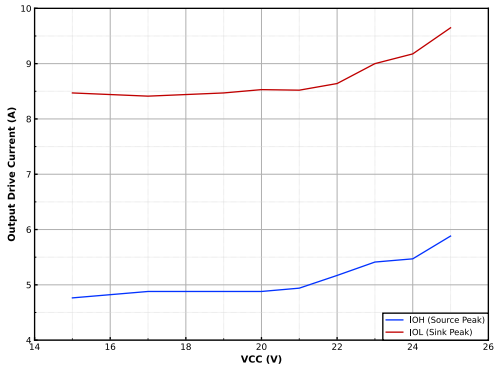
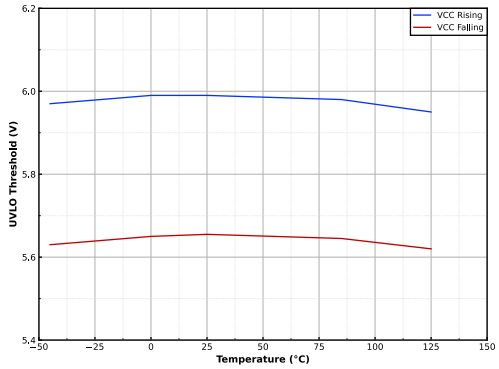
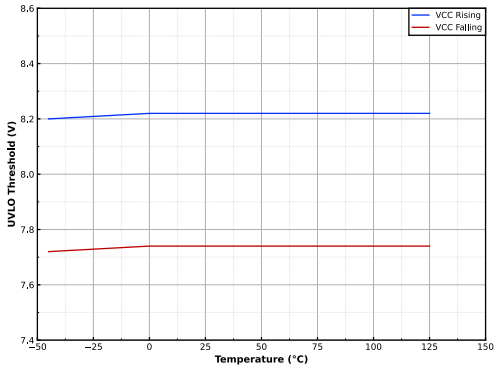


Figure 8. Output Drive Current vs. V_{CC}



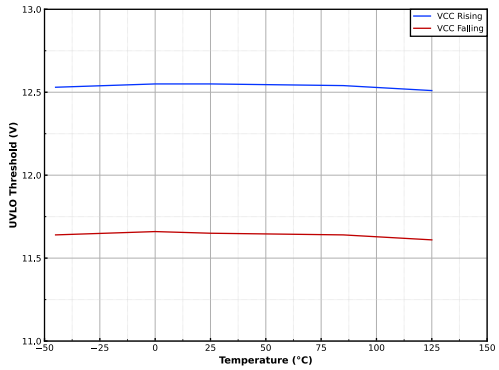
6.3-V UVLO Version

Figure 9. UVLO Threshold vs. Temperature



8-V UVLO Version

Figure 10. UVLO Threshold vs. Temperature



13.3-V UVLO Version

Figure 11. UVLO Threshold vs. Temperature

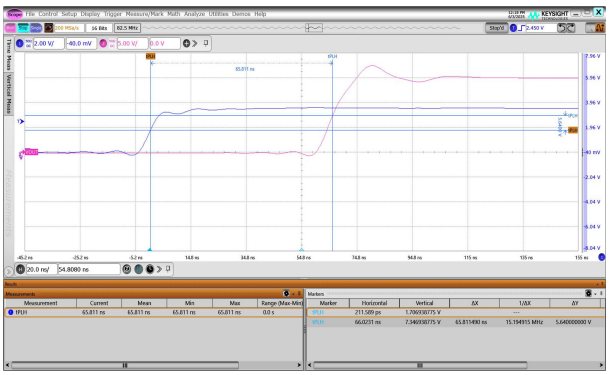


Figure 12. Output Rising Edge

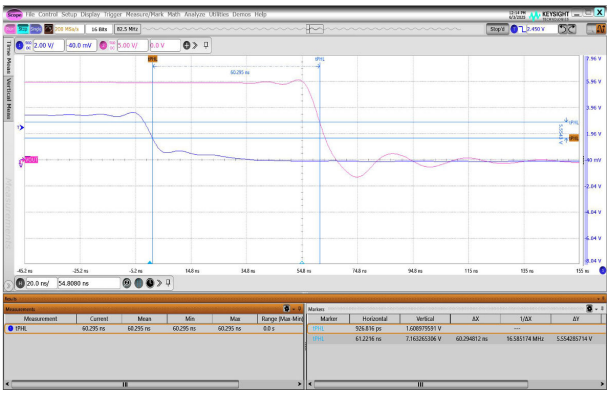


Figure 13. Output Falling Edge

Detailed Description

Overview

The TPM23525 is a single-channel isolated gate driver for MOSFETs, IGBTs, and SiC FETs with an optocoupler-compatible input stage which is an emulated diode. It has a 35-V maximum operating driver voltage, which is especially suitable for high-power fast-transient IGBT / SiC applications.

The TPM23525 is designed to replace the optocoupler gate driver with an industry-standard wide-body 6-pin package WSOP6, with more than 8.5-mm creepage and clearance to withstand over 1060-V_{RMS} working voltage, reinforced isolation, and 5-kV_{RMS} for 60 s and a surge rating of 8-kV V_{PK}. 3PEAK proprietary isolation technology supports common-mode transient immunity of greater than 150 kV/μs.

Functional Block Diagram

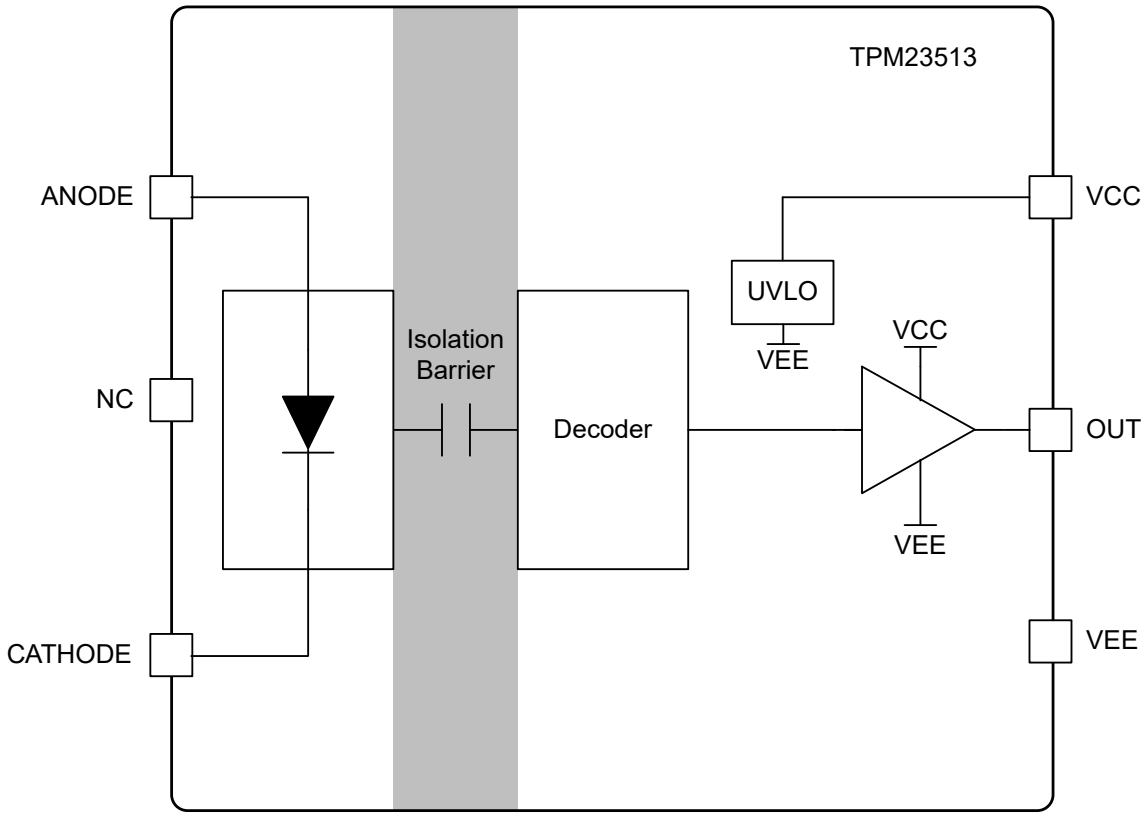


Figure 14. Functional Block Diagram

Feature Description

Emulated Diode Input

The input stage of the TPM23525 is an emulated diode input to be pin-to-pin compatible with the optocoupler input. Working like an opto-diode, when the current flows from ANODE and CATHODE, the forward voltage drop between ANODE and CATHODE is typical 2.1 V. An external resistor can be placed on the ANODE side or the CATHODE side or both to limit the current. 3PEAK recommends that the forward current should be from 7 mA to 30 mA. When the input current is higher than the threshold current I_{FTH_R}, the TPM23525 internal isolation transmitter starts to send CMTI-optimized high-frequency On-Off-Keying (OOK) signals through the double-capacitive silicon dioxide (SiO_2) isolation layer. 3PEAK proprietary isolation technology provides high CMTI performance against fast dV/dt scenarios, which is especially useful for latest-generation applications like SiC FETs.

Decoder & Output Stage

The high-frequency signal is converted by the decoder via a double-capacitive insulation barrier as the output stage's input. The rail-to-rail output stage provides a high-peak current during the output slewing. The output V_{CC} supports a maximum 35-V input.

The TPM23525 output stage is able to deliver high current sourcing up to 5 A and sinking up to 5 A with low propagation delay.

Protection

Under-Voltage Lock Out (UVLO)

The device has a UVLO feature to monitor the voltage between V_{CC} and V_{EE} to prevent under-driven working conditions. When V_{CC} rises above the UVLO rising threshold, the output follows the device input; when V_{CC} falls below the UVLO falling threshold longer than the deglitch timer, the device gets into UVLO protection and holds the output low. The UVLO has a hysteresis of $UVLO_{HYS}$ to prevent power supply noises during switching.

Active Pulldown

The output stage has an under-voltage lock-out feature to protect the output driver from malfunction during low-voltage operation. When V_{CC} is lower than the UVLO threshold, the output will be driven low. When V_{CC} is higher than the UVLO threshold, the output will be operated according to the input bias state. When V_{CC} is unbiased, the output will be pulled lower to 2 V to avoid false turning on.

Short Circuit Clamping

The device has a short-circuit clamping feature to clamp driver output voltage and protect the IGBT/MOSFET gate from over-voltage breakdown or degradation. The short-circuit can withstand 500 mA for 10 μs and a continuous current of 20 mA. In case higher current conduction is required, 3PEAK recommends using external Schottky diodes in parallel.

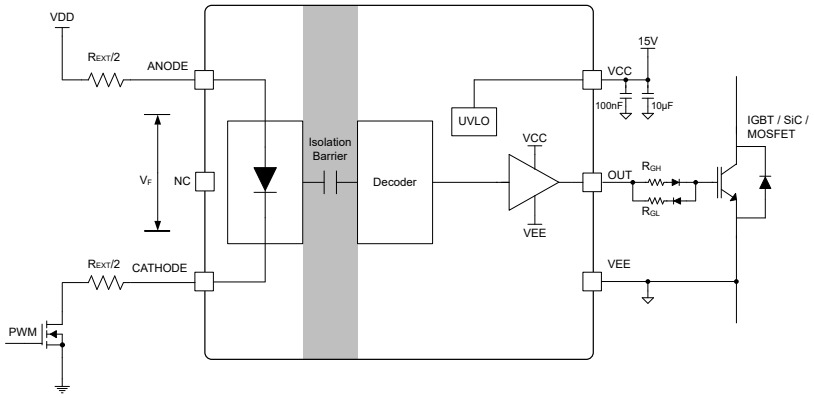
Application and Implementation

> Note
>
> Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

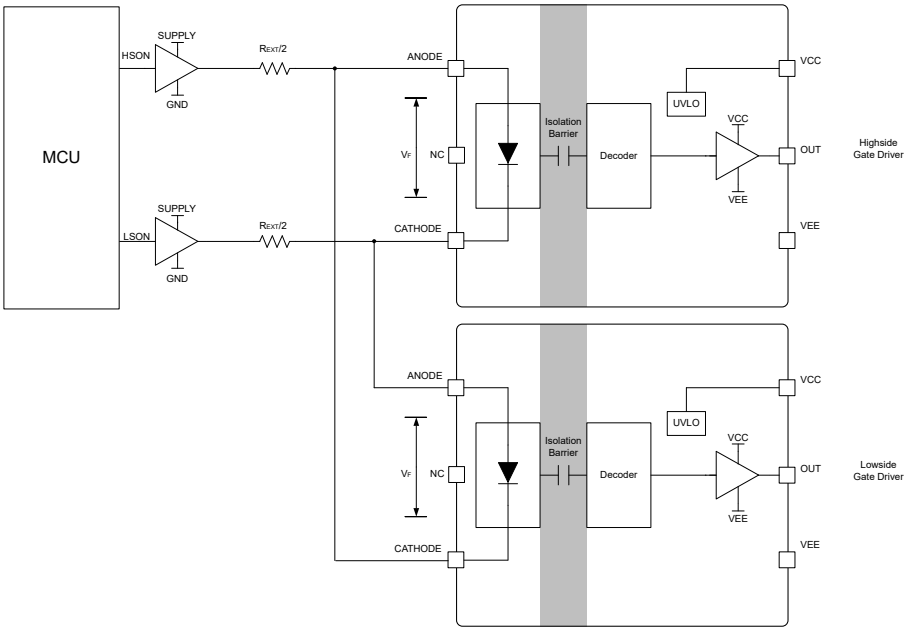
Typical Application

The TPM23525 supports pin-to-pin replacement of common opto-coupler-based gate drivers. A serial resistor is added to the input path to limit current between 7 mA and 25 mA.

Low-side NMOS Driving Stage



Half-bridge Driver with Interlock



For most half-bridge driver applications, 2 pcs of the TPM23525 can be used with MCU interlock feature, and prevent shoot-through since the input will reject when LSON and HSON are both at high state or low state. The reverse input voltage between ANODE and CATHODE can be as high as SUPPLY voltage, 3PEAK recommends supply voltage be set below 5.5-V considering the 6.5-V input reverse breakdown voltage.

Input Resistor

A common MCU cannot supply a large enough current to turn on the input diode. 3PEAK recommends using an NMOS FET to drive with current-limiting resistors. The serial resistor is used to limit diode current as below equation, 3PEAK recommends using R_{EXT} between 200 Ω and 300 Ω.

$$R_{EXT} = \frac{V_{SUPPLY} - V_F}{I_F} - R_{BUFFER} \quad (1)$$

A 10-μF VCC capacitor and 100-nF decoupling capacitor should be placed close to the device VCC node.

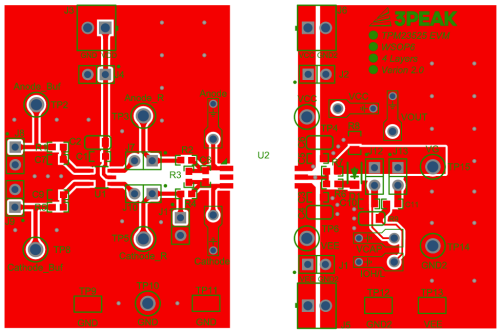
The power supply between VCC and VEE must be greater than UVLO. 3PEAK recommends 15 V and above. In case of a negative shutdown voltage is needed, 3PEAK recommends separating VEE from the IGBT emitter/MOSFET source node. and tie VEE to negative voltage with reference to the IGBT emitter / MOSFET source node. Total VCC-VEE should be smaller than 35 V.

Layout

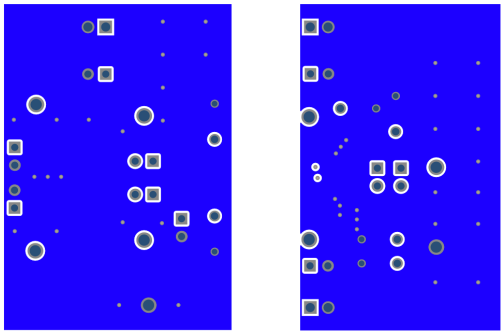
Layout Guideline

- For voltage mode input drivers, a low ESR and ESL capacitor should be placed close to the VCC and VEE pins, and the loop from VCC to VEE should be made small.
- For current mode input drivers, a low ESR and ESL capacitor should be placed close to the Cathode and Anode pins.
- To minimize the inductance of the drive circuit loop, the driver should be placed close to the transistor.
- The Miller clamp trace should be directly connected to the transistor's gate, and the trace should be kept short.
- To ensure isolation between the primary and secondary sides, avoid placing any PCB traces or copper directly below the driver device. A PCB cutout or groove is recommended to increase the creepage distance.
- To enhance thermal performance, it is recommended to enlarge the PCB copper connected to VCC and VEE.

Layout Recommendations

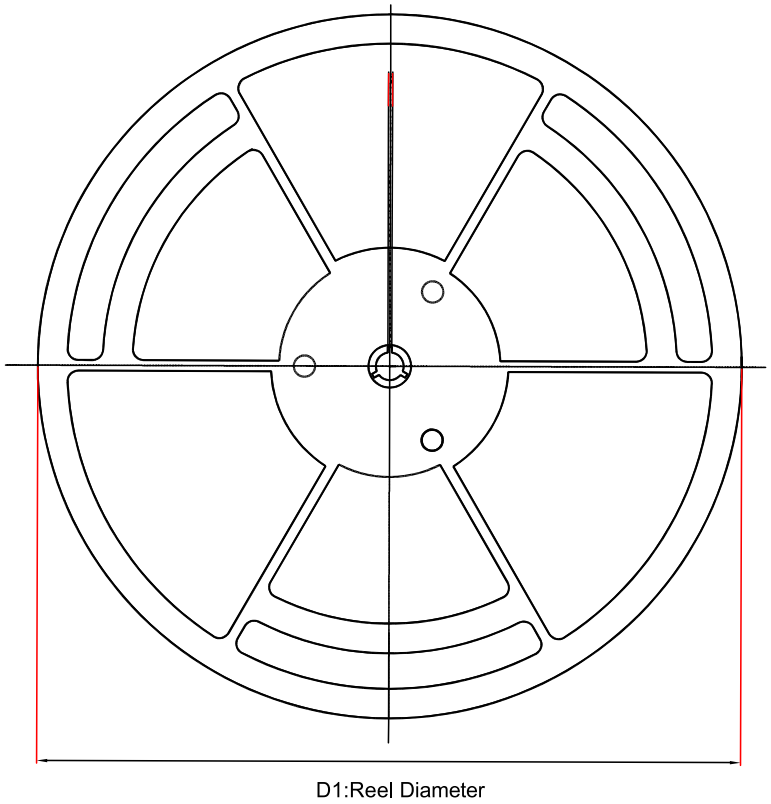


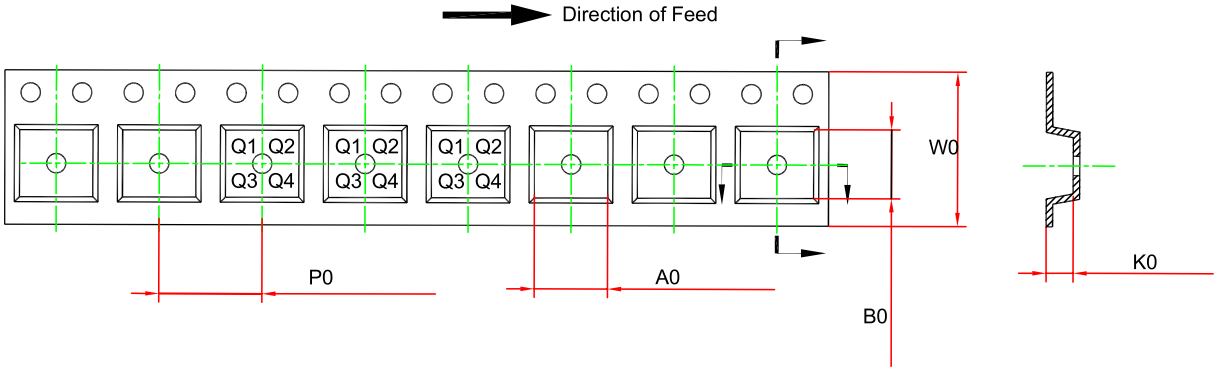
Top Layer



Bottom Layer

Tape and Reel Information



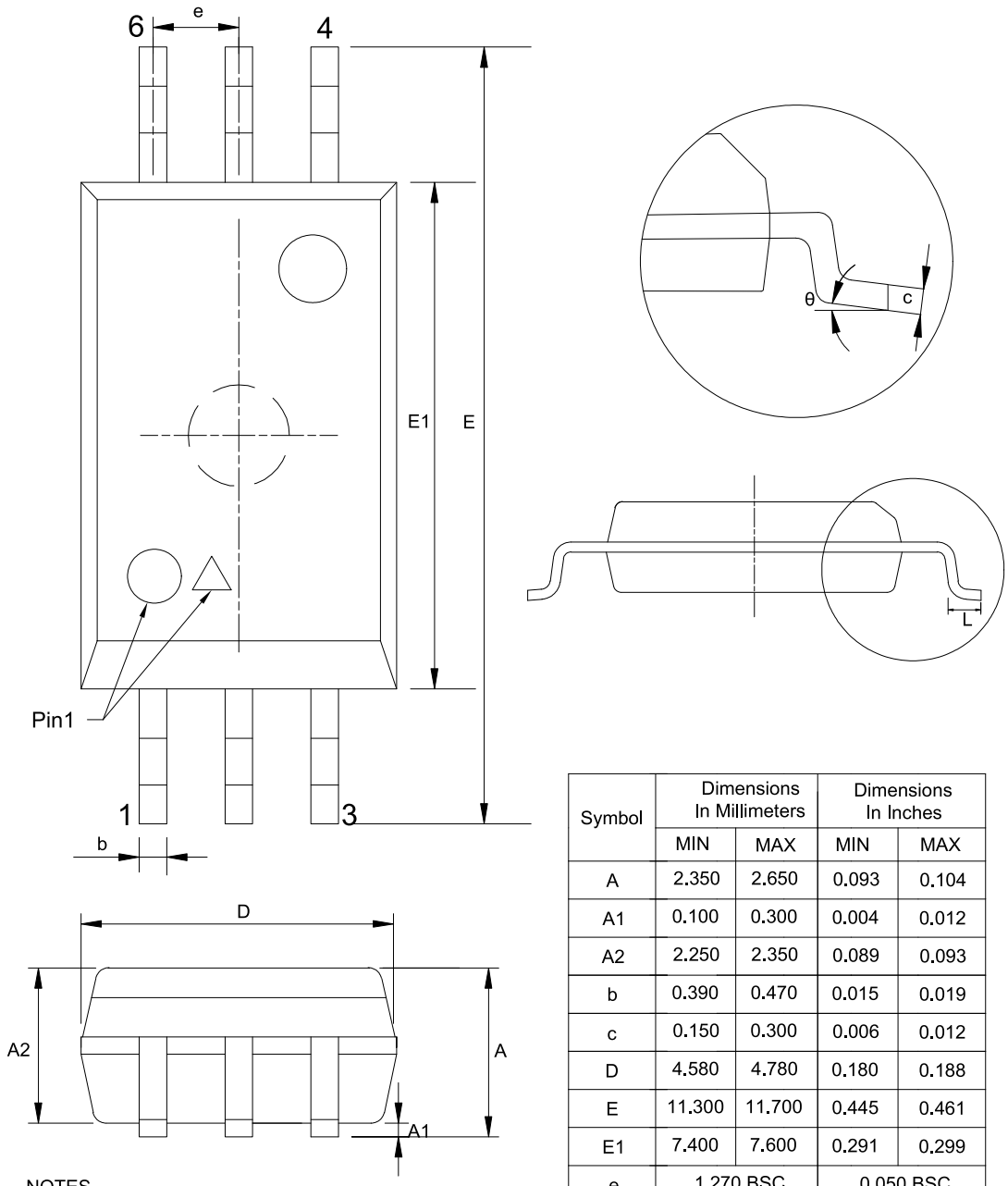


Order Number	Package	D1 (mm)	W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	W0 (mm)	Pin1 Quadrant
TPM23525A-SOER	WSOP6	330	21.6	11.95	5.2	3	16	16	Q1
TPM23525B-SOER	WSOP6	330	21.6	11.95	5.2	3	16	16	Q1
TPM23525C-SOER	WSOP6	330	21.6	11.95	5.2	3	16	16	Q1
TPM23525D-SOER	WSOP6	330	21.6	11.95	5.2	3	16	16	Q1

Package Outline Dimensions

WSOP6

Package Outline Dimensions SOE(WSOP-6-A)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	2.350	2.650	0.093	0.104
A1	0.100	0.300	0.004	0.012
A2	2.250	2.350	0.089	0.093
b	0.390	0.470	0.015	0.019
c	0.150	0.300	0.006	0.012
D	4.580	4.780	0.180	0.188
E	11.300	11.700	0.445	0.461
E1	7.400	7.600	0.291	0.299
e	1.270 BSC		0.050 BSC	
L	0.500	1.000	0.020	0.039
θ	0	8°	0	8°

NOTES

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

Order Information

Order Number	Operating Ambient Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPM23525A-SOER (1)	−40°C to 125°C	WSOP6	M525A	3	1000	Green
TPM23525B-SOER	−40°C to 125°C	WSOP6	M525B	3	1000	Green
TPM23525C-SOER	−40°C to 125°C	WSOP6	M525C	3	1000	Green
TPM23525D-SOER (1)	−40°C to 125°C	WSOP6	M525D	3	1000	Green

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.

(1) Contact 3PEAK representatives for more information.

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